OIPE JC34
JAN 22 2004
PATENT & TRADEMARK OFFICE

Docket No: 740756-2675

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Divisional Patent Application of	)
Hongyong ZHANG	)
Application Serial No. 10/726,529	) Art Unit: 2823
Filed: December 04, 2003	) Examiner: K. Nguyen
For: METHOD FOR FORMING A	)
SEMICONDUCTOR DEVICE	) Date: January 22, 2004

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. §1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98.

The references listed on the attached Form PTO-1449 were cited in parent application Serial No. 09/222,776 filed December 30, 1998, and its predecessors application Serial Nos. 08/300,938 and 07/956,860, from which priority is claimed under 35 U.S.C. 120. Consequently, copies of the documents are not required.

It is requested that the accompanying PTO-1449 be considered and made of record in the above-identified application. To assist the Examiner, the documents are listed on the attached form PTO-1449. It is respectfully requested that an Examiner initialed copy of this form be returned to the undersigned.

Respectfully submitted,

By _____
Jeffrey L. Costellia
Registration No. 35,483

NIXON PEABODY LLP
401 9th Street, N.W.
Suite 900
Washington, D.C. 20004-2128

(202) 585-8000
NVA283469.1

OIPE JC34 JAN 22 2004 PATENT & TRADEMARK OFFICE

Please type a plus sign (+) inside this box →

PTO/SB/08A (08-00)
Approved for use through 10/31/2002. OMB 0651-0031
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	1	of	4

Complete if Known	
Application Number	10/726,529
Filing Date	December 4, 2003
First Named Inventor	Hongyong ZHANG
Group Art Unit	2823
Examiner Name	K. Nguyen
Attorney Docket Number	740756-2675

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	U.S. Patent Document Number	Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		5,766,344		Zhang et al	06/16/98	
		4,266,986		Benton et al	05/12/91	
		4,552,595		Hoga	11/12/85	
		4,555,301		Gibson et al	11/25/85	
		4,569,697		Tsu et al	02/11/86	
		4,638,110		Erbert	01/20/87	
		5,306,651		Masumo et al	04/26/94	
		5,352,291		Zhang et al	10/04/94	
		5,372,836		Imahashi et al	12/13/94	
		4,933,298		Hasegawa	06/12/90	
		4,885,260		Ban et al	12/05/89	
		3,771,026		Asai et al	11/06/73	
		5,114,876		Weiner	05/19/92	
		4,758,533		Magee et al.	07/19/88	
		US-5,151,383		Meyerson et al.	09/29/1992	
		US-5,861,337		Zhang et al.	01/19/1999	
		US-5,849,043		Zhang et al.	12/15/1998	
		US-5,424,244		Zhang et al.	06/13/1995	
		US-5,200,630		Nakamura et al.	04/1993	
		US-5,104,455		Yokota et al.	04/1992	

Examiner Signature:	**Date Considered:**

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609.. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

OIPE JC37 JAN 22 2004 PATENT & TRADEMARK OFFICE

Form PTO-1449 (Rev. 8-83) U.S. Department of Commerce Patent and Trademark Office	Attorney Docket:	Serial No.
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	740756-2675	10/726,529
	Applicant: Hongyong ZHANG	
	Filing Date: December 4, 2003	Group: 2823

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document Office[3]	Foreign Patent Document Number[4] (if known)	Kind Code[5]	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
		JP	02-224339		Masayoshi et al.	09/06/90		Full
		JP	57-202729		Tadashi et al.	12/11/82		Abstract
		JP	01-259530		Asakawa	10/17/89		Full
		JP	03-148836		Kazuhiro et al.	06/25/91		Abstract
		JP	61-255016		Yamazaki	11/86		Abstract
		JP	58-092216		Haruhiko et al.	06/83		Abstract
		JP	56-142651		Morikuri	11/81		Abstract
		JP	86115			03/90		Abstract
		JP	02-114521		Noguchi et al.	04/26/1990		Abstract
		JP	03-178125		Arima et al.	08/02/1991		Abstract
		JP	60-216538		Shimizu et al.	10/30/1985		Abstract
		JP	60-245174		Yamazaki	12/04/1985		Abstract
		JP	62-264619		Samejima	11/17/1987		Abstract
		JP	61-199640		Samejima et al.	09/04/1986		Abstract

Examiner Signature:	Date Considered:

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

OIPE JC54 JAN 22 2004 PATENT & TRADEMARK OFFICE

Form PTO-1449 (Rev. 8-83) U.S. Department of Commerce Patent and Trademark Office	Attorney Docket:	Serial No.
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	740756-2675	10/726,529
	Applicant: Hongyong ZHANG	
	Filing Date: December 4, 2003	**Group**: 2823

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		Kawachi et al., "Large-Area Doping Process for Fabrication of poly-Si Thin Film Transistors Using Bucket Ion Source and XeCl Excimer Laser Annealing," Japanese Journal of Applied Physics, Vol. 29, No. 12, December 1990, pp. L2370-2372.
		Inoue et al., "Low Temperature CMOS Self-Aligned Poly-Si TFTs and Circuit Scheme Utilizing New Ion Doping and Masking Technique", 1991 IEEE 20.1.1-20.1.4 IEDM, August 12, 1991, pp. 555-558.
		Stringfellow, "Vapor Phase Growth", Crystal Growth, Vol. 16, 2nd Edition, Pampline, Chapter 5, pp. 181-202.
		Takenaka et al., "High Mobility Poly-Si Thin Film Transistors Using Solid Phase Crystallized A-Si Films Deposited by Plasma-Enhanced Chemical Vapor Deposition", Japanese Journal of Applied Physics, Vol. 29, No. 12, December 1990.
		Boyd, "Laser-Enhanced Oxidation of Si", Applied Physics Letters, Vol. 42, No. 8, pp. 728-30.
		Craciun et al., "Direct Laser Synthesis of Thin Silicon and Germanium Nitride/Oxynitride Layers", Nucl. Instrum. Methods Phys. Res. B, Beam Interact. Mater At., Vol. B65, No. 1-4, pp. 115-18 (March 1992).
		Craciun et al., "Direct Oxynitride Synthesis by Multipulse Excimer Laser Irradiation of Silicon Wafers in a Nitrogen-Containing Ambient Environment", J. Appl. Phys, Vol. 68, No. 5, September 1, 1990, pp. 2509-11.
		Russell et al., "Bipolar Transistors in Silicon-on-Sapphire (SOS) Effects of Nanosecond Thermal Processing", IEEE SOS/SOI Tech. Conf. Proceedings October 24, 1990.
		Wolf et al., Silicon Processing for the VLSI Era Volume 1: Process Technology, Lattice Press, Sunset Beach, CA, (1989), pp. 471, 476-479.
		Carey et al., "Submicrometer CMOS Device Fabrication Using Gas Immersion Laser Doping (GILD)", IEEE Transactions on Eletcron Devices, Vol. 35, No. 12, December 1988, p. 2429.
		Weiner et al., "Thin-Base Bipolar Transistor Fabrication Using Gas Immersion Laser Doping", IEEE Electron Dev. Lett., Vol. 10, No. 6, (1989), pp. 260-263.
		Turner et al., "Gas Immersion Laser Diffusion for Efficient Cell Fabrication and Grain Boundary Research", 16th IEEE Photovoltaic Specialist Conference, San Diego, CA, September 27-30, 1982, pp. 775-780.
		Carey et al., "Ultra-Shallow High Concentration Boron Profiles for CMOS Processing", IEEE Electron Dev. Lett., Vol. EDL-6, No. 6, (1985), pp. 291-293
		Carey et al., "Fabrication of Submicrometer MOSFETS Using Gas Immersion Laser Doping (GILD)," IEEE Electron Dev. Lett., Vol. EDL-7, No. 7, (1986), pp. 440-442.
		Weiner et al., "Measurement of Melt Depth Limited Diffusion in Gas Immersion Laser Doped Silicon Using an Improved Laser System," (In Proceedings of the Symposium on Laser Processing for Microelectronic Applications) (1988), pp. 53-61.

Examiner Signature:	**Date Considered:**

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

OIPE JC34
JAN 22 2004
PATENT & TRADEMARK OFFICE

Form PTO-1449 (Rev. 8-83) U.S. Department of Commerce Patent and Trademark Office	Attorney Docket:	Serial No.
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	740756-2675	10/726,529
	Applicant: Hong ZHANG	
	Filing Date: December 4, 2003	**Group**: 2823

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		Matsuo et al., "Low-Temperature Activation of Impurities Implanted by Ion Doping Technique for Poly-Si Thin-Film Transistors", Jpn. J. Appl. Phys., Vol. 31, Part I, No. 12B, December 1992, pp. 4567-4569
		Mishima et al., "Implantation Temperature Effect on Polycrystalline Silicon by Ion Shower Doping", J. Appl. Phys., Vol. 74, No. 12, December 15, 1993, pp. 7114-7117
		Bruno et al., RF Plasma deposition of a-silicon-germanium alloys: evidence for chemisorption-based growth process, pp. 934-939, (IEEE), December, 1990.

Examiner Signature:	**Date Considered:**

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.